

2SC2613

Silicon NPN Triple Diffused

HITACHI

ADE-208-886 (Z)

1st. Edition

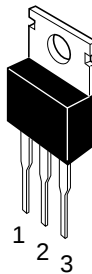
Sep. 2000

Application

High voltage, high speed and high power switching

Outline

TO-220AB



1. Base
2. Collector (Flange)
3. Emitter

Absolute Maximum Ratings ($T_a = 25^{\circ}\text{C}$)

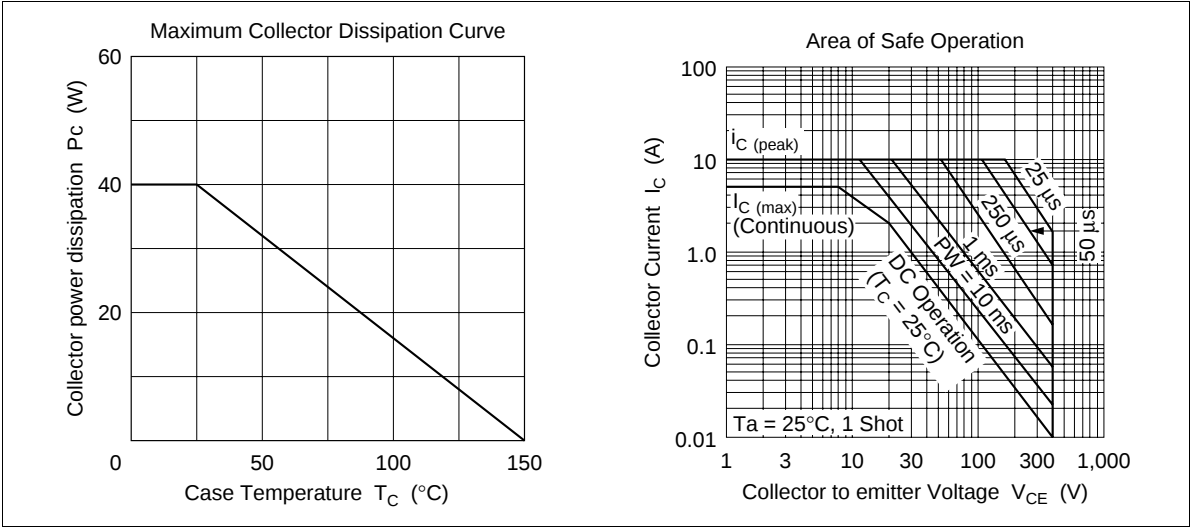
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	500	V
Collector to emitter voltage	V_{CEO}	400	V
Emitter to base voltage	V_{EBO}	7	V
Collector current	I_{C}	5	A
Collector peak current	$I_{\text{C(peak)}}$	10	A
Base current	I_{B}	2.5	A
Collector power dissipation	P_{C}^{*1}	40	W
Junction temperature	T_{j}	150	$^{\circ}\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^{\circ}\text{C}$

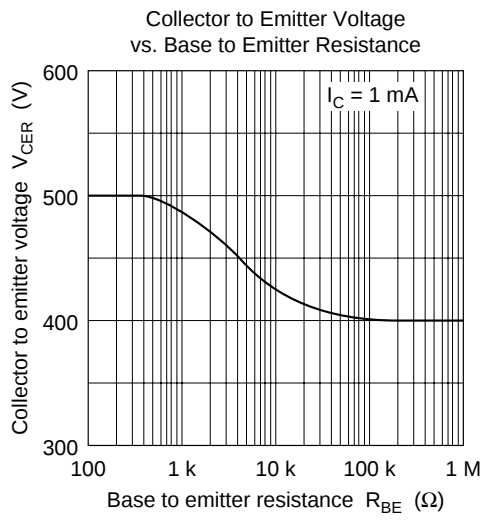
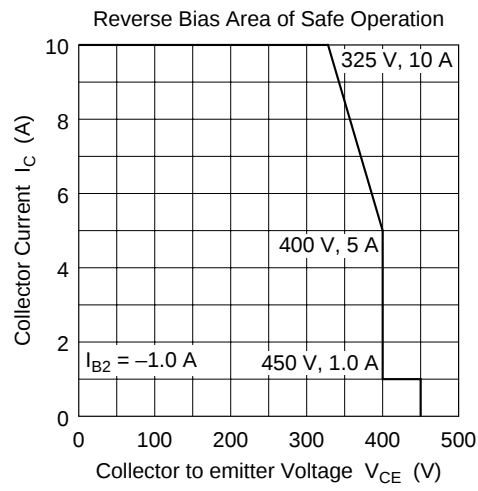
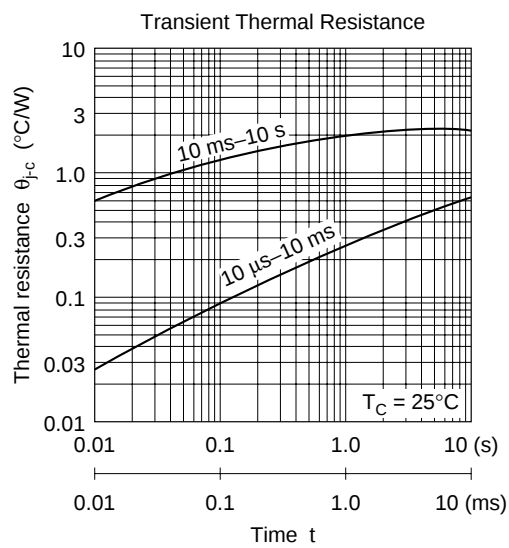
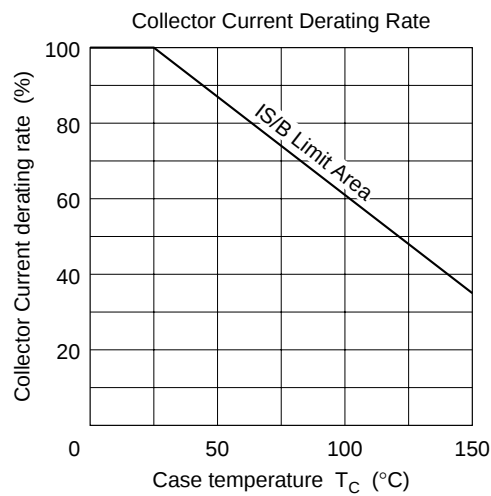
Note: 1. Value at $T_{\text{C}} = 25^{\circ}\text{C}$.

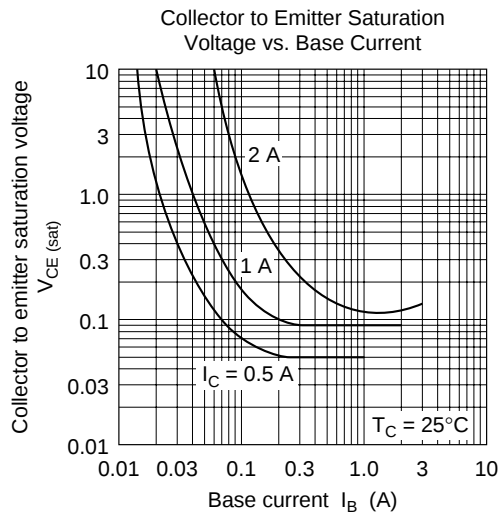
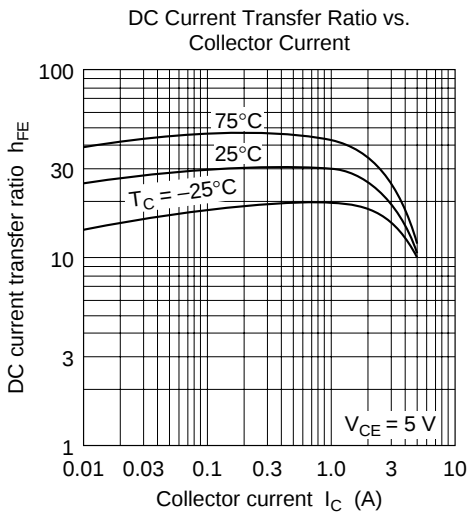
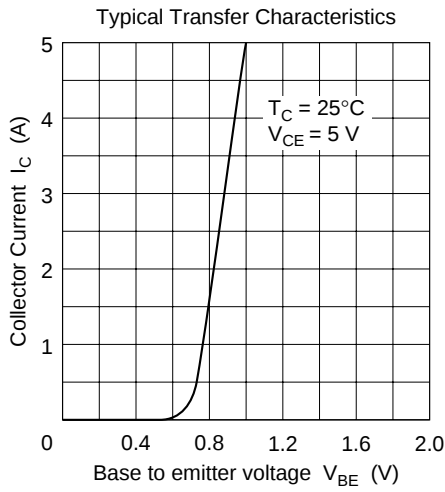
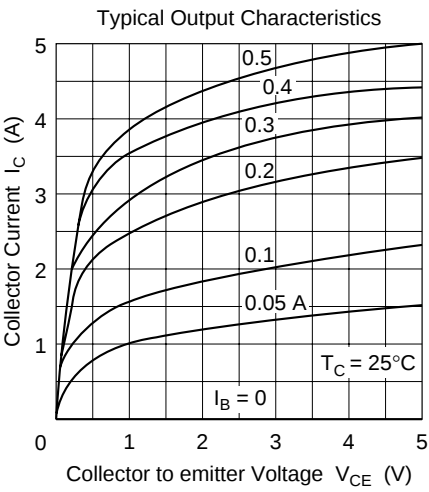
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter sustain voltage	$V_{CEO(sus)}$	400	—	—	V	$I_C = 0.2\text{ A}$, $R_{BE} = \infty$, $L = 100\text{ mH}$
	$V_{CEX(sus)}$	400	—	—	V	$I_C = 5\text{ A}$, $I_{B1} = -I_{B2} = 1\text{ A}$ $V_{BE} = -5\text{ V}$, $L = 180\text{ }\mu\text{H}$, Clamped
Emitter to base breakdown voltage	$V_{(BR)EBO}$	7	—	—	V	$I_E = 10\text{ mA}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	100	μA	$V_{CB} = 400\text{ V}$, $I_E = 0$
	I_{CEO}	—	—	100	μA	$V_{CE} = 350\text{ V}$, $R_{BE} = \infty$
DC current transfer ratio	h_{FE1}	15	—	—		$V_{CE} = 5\text{ V}$, $I_C = 2.5\text{ A}^{*1}$
	h_{FE2}	7	—	—		$V_{CE} = 5\text{ V}$, $I_C = 5\text{ A}^{*1}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	1.0	V	$I_C = 2.5\text{ A}$, $I_B = 0.5\text{ A}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	—	1.5	V	$I_C = 2.5\text{ A}$, $I_B = 0.5\text{ A}^{*1}$
Turn on time	t_{on}	—	—	1.0	μs	$I_C = 5\text{ A}$, $I_{B1} = -I_{B2} = 1\text{ A}$,
Storage time	t_{stg}	—	1.2	2.5	μs	$V_{CC} \cong 150\text{ V}$
Fall time	t_f	—	—	1.0	μs	

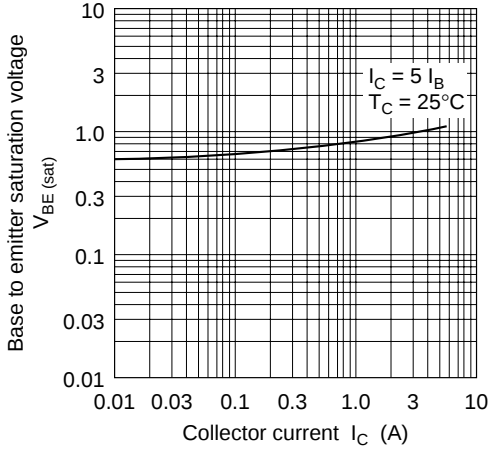
Note: 1. Pulse test.



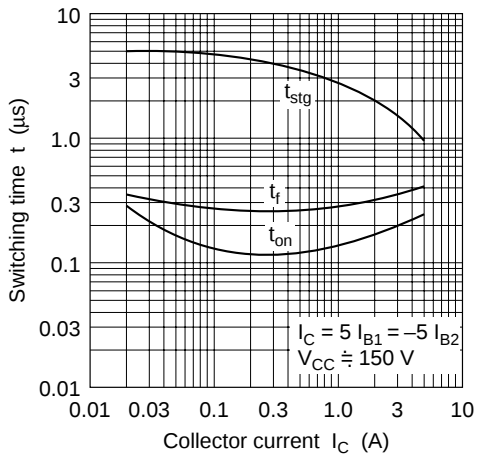




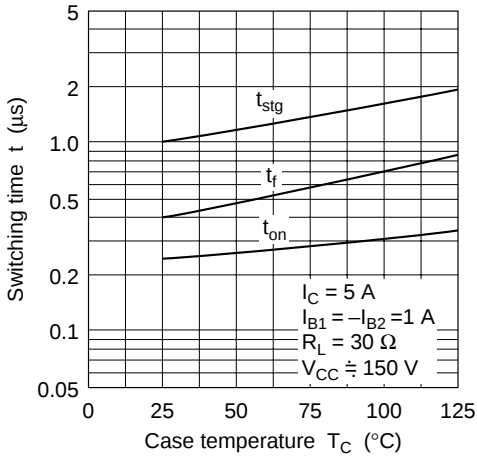
Base to Emitter Saturation Voltage
vs. Collector Current



Switching Time vs. Collector Current

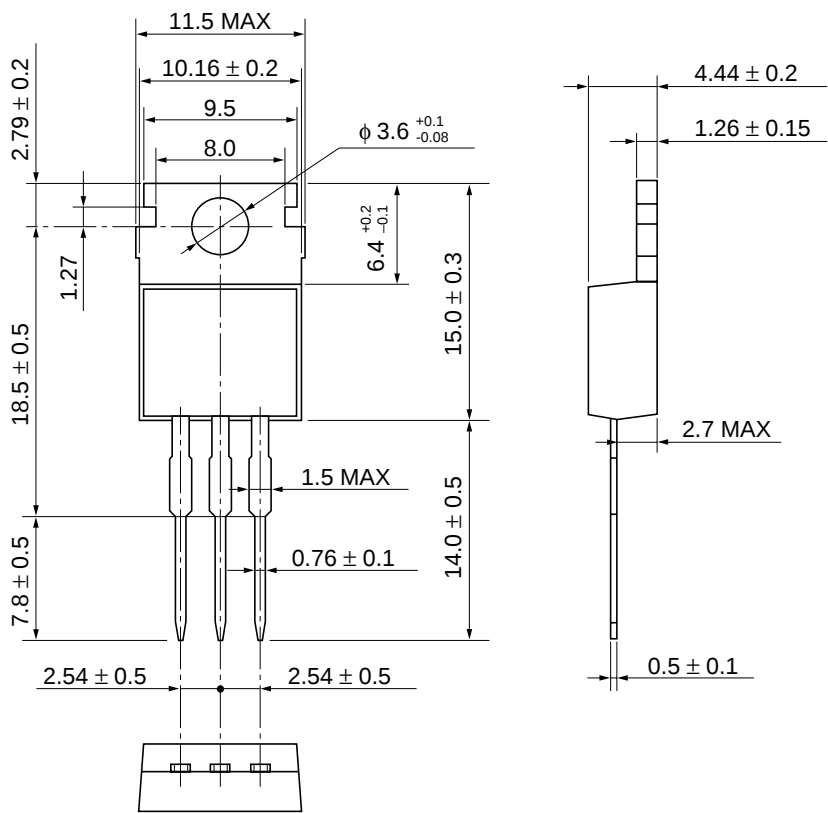


Switching Time vs. Case Temperature



Package Dimensions

Unit: mm



Hitachi Code	TO-220AB
JEDEC	Conforms
EIAJ	Conforms
Mass (reference value)	1.8 g

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HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose, CA 95134 Tel: <1> (408) 433-1990 Fax: <1> (408) 433-0223	Hitachi Europe GmbH Electronic Components Group Dornacher Straße 3 D-85622 Feldkirchen, Munich Germany Tel: <49> (89) 9 9180-0 Fax: <49> (89) 9 29 30 00
	Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park Lower Cookham Road Maidenhead Berkshire SL6 8YA, United Kingdom Tel: <44> (1628) 585000 Fax: <44> (1628) 585160

Hitachi Asia Ltd. Hitachi Tower 16 Collyer Quay #20-00, Singapore 049318 Tel: <65>-538-6533/538-8577 Fax: <65>-538-6933/538-3877 URL: http://www.hitachi.com.sg	Hitachi Asia Ltd. (Taipei Branch Office) 4/F, No. 167, Tun Hwa North Road, Hung-Kuo Building, Taipei (105), Taiwan Tel: <886>-(2)-2718-3666 Fax: <886>-(2)-2718-8180 Telex: 23222 HAS-TP URL: http://www.hitachi.com.tw
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Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon,
Hong Kong
Tel: <852>-(2)-735-9218
Fax: <852>-(2)-730-0281
URL: <http://www.hitachi.com.hk>

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